

 D.G.M.E.	30-200A	版本号: V1.0
	方片晶闸管系列 Thyristor	

产品概述 General Description

方片晶闸管采用双台面结构，复合玻璃钝化PN结表面保护工艺技术，单向触发导通，抗干扰能力强，可靠性高。

30-200A Thyristor is fabricated using two-side diffusion processes ,the junction termination areas are passivated with glass. thanks to reliability and high blocking voltage,the SCR series is suitable for Controlled rectifier circuits ,Solid state relays

产品特点 MAIN FEATURES

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| <ul style="list-style-type: none"> ● 表面玻璃钝化，可靠性高 ● 阻断电压高 ● 通态压降低 抗浪涌电流能力强 | <ul style="list-style-type: none"> ● Glass-Passivated Surface For Reliability ● High blocking voltage ● Low on-state voltage and high I_{TSM} |
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应用领域 Applications

主要应用于整流控制电路、固态继电器等。
Controlled rectifier circuits ,Solid state relays .

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
$I_T (RMS)$	30-200	A
V_{DRM}/V_{RRM}	1600	V
I_{GT}	100	mA

组件示意图outing drawing:

KP30 KP40	KP50 KP60 KP80	KP60 KP90	KP90 KP100 KP110 KP130 KP180	KP150

组件技术参数 (除非另有规定, $T_a=25^\circ\text{C}$) ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$, unless otherwise specified)

组件型号 Model	铜片尺寸 (mm) Mechanical Data (mm)		电特性参数 Parameter						
	长	宽	$V_{\text{DRM}}/V_{\text{RRM}}$ DC. V	I_{T} (AV) A	$V_{\text{T}}@I_{\text{T(RMS)}}$ V	dv/dt V/ μ s	di/dt A/ μ s	I_{GT} mA	$I_{\text{D/R}}$ mA
KP3016	8.0	8.0	≥ 1600	30	1.3	500	150	≤ 100	≤ 2
KP4016	9.0	9.0	≥ 1600	40	1.3	500	150	≤ 100	≤ 2
KP5016	10.0	10.0	≥ 1600	50	1.3	500	150	≤ 100	≤ 2
KP6016	11.0	11.0	≥ 1600	60	1.4	500	150	≤ 150	≤ 4
KP8016	13.0	13.0	≥ 1600	80	1.4	500	150	≤ 150	≤ 4
KP9016	13.8	13.8	≥ 1600	90	1.4	500	150	≤ 150	≤ 4
KP10016	15.0	15.0	≥ 1600	100	1.4	500	150	≤ 150	≤ 4
KP11016	16.0	16.0	≥ 1600	110	1.4	500	150	≤ 150	≤ 10
KP13016	18.0	18.0	≥ 1600	130	1.4	500	150	≤ 150	≤ 10
KP15016	21.0	18.0	≥ 1600	150	1.4	500	150	≤ 150	≤ 10
KP18016	23.0	23.0	≥ 1600	180	1.4	500	150	≤ 150	≤ 10